In the Claims:

Claims 1-21 (canceled)

Claim 22 (new): A FET situated over a substrate, said FET comprising:

a channel situated in said substrate;

a first gate dielectric situated over said channel, said first gate dielectric having a first coefficient of thermal expansion;

a first gate electrode situated over said first gate dielectric, said first gate electrode having a second coefficient of thermal expansion;

wherein said second coefficient of thermal expansion is different than said first coefficient of thermal expansion so as to cause an increase in carrier mobility in said FET;

a second gate electrode situated between said first gate electrode and said first gate dielectric, said second gate electrode having a third coefficient of thermal expansion, said third coefficient of thermal expansion being greater than said first coefficient of thermal expansion and said third coefficient of thermal expansion being less than said second coefficient of thermal expansion so as to cause a tensile strain in said channel, said tensile strain causing said increase in said carrier mobility.

Claims 23 (new): The FET of claim 22 further comprising a second gate dielectric situated between said first gate dielectric and said substrate, said second gate

PAGE 5/11 * RCVD AT 11/5/2009 6:35:38 PM [Eastern Standard Time] * SVR:USPTO-EFXRF-6/21 * DNIS:2738300 * CSID:949 282 1002 * DURATION (mm-ss):02-36

dielectric having a third coefficient of thermal expansion, said third coefficient of thermal expansion being less than said first coefficient of thermal expansion and said second coefficient of thermal expansion being greater than said first coefficient of thermal expansion so as to cause a tensile strain in said channel, said tensile strain causing said increase in said carrier mobility.

Claim 24 (new): The FET of claim 22 further comprising a gate liner situated adjacent to said first gate dielectric and a gate spacer situated adjacent to said gate liner, said gate liner having a third coefficient of thermal expansion and said gate spacer having a fourth coefficient of thermal expansion, said fourth coefficient of thermal expansion being greater than said third coefficient of thermal expansion so as to cause a tensile strain in said channel.

Claim 25 (new): A FET situated over a substrate, said FET comprising a channel situated in said substrate, a first gate dielectric situated over said channel, said first gate dielectric having a first coefficient of thermal expansion, a first gate electrode situated over said first gate dielectric, said first gate electrode having a second coefficient of thermal expansion, said FET being characterized in that:

said second coefficient of thermal expansion being different than said first coefficient of thermal expansion so as to cause an increase in carrier mobility in said FET;

PAGE 6/11 * RCVD AT 11/5/2009 6:35:38 PM [Eastern Standard Time] * SVR:USPTO-EFXRF-6/21 * DNIS:2738300 * CSID:949 282 1002 * DURATION (mm-ss):02-36

a second gate electrode situated between said first gate electrode and said first gate dielectric, said second gate electrode having a third coefficient of thermal expansion, said third coefficient of thermal expansion being greater than said first coefficient of thermal expansion and said third coefficient of thermal expansion being less than said second coefficient of thermal expansion so as to cause a tensile strain in said channel, said tensile strain causing said increase in said carrier mobility.

Claim 26 (new): The FET of claim 25 further comprising a second gate dielectric situated between said first gate dielectric and said substrate, said second gate dielectric having a third coefficient of thermal expansion, said third coefficient of thermal expansion being less than said first coefficient of thermal expansion and said second coefficient of thermal expansion being greater than said first coefficient of thermal expansion so as to cause a tensile strain in said channel, said tensile strain causing said increase in said carrier mobility.

Claim 27 (new): The FET of claim 25 further comprising a gate liner situated adjacent to said first gate dielectric and a gate spacer situated adjacent to said gate liner, said gate liner having a third coefficient of thermal expansion and said gate spacer having a fourth coefficient of thermal expansion, said fourth coefficient of thermal expansion being greater than said third coefficient of thermal expansion so as to cause a tensile strain in said channel.

PAGE 7/11 * RCVD AT 11/5/2009 6:35:38 PM [Eastern Standard Time] * SVR:USPTO-EFXRF-6/21 * DNIS:2738300 * CSID:949 282 1002 * DURATION (mm-ss):02-36

Claim 28 (new): A FET situated on a substrate, said FET comprising:

a channel situated in said substrate;

a gate stack situated over said channel;

a first gate dielectric situated in said gate stack, said first gate dielectric having a first coefficient of thermal expansion;

a first gate electrode situated over said first gate dielectric, said first gate electrode having a second coefficient of thermal expansion;

wherein said second coefficient of thermal expansion is different than said first coefficient of thermal expansion so as to cause a strain in said channel, said strain causing an increase in carrier mobility in said FET;

a second gate electrode situated between said first gate electrode and said first gate dielectric, said second gate electrode having a third coefficient of thermal expansion, said third coefficient of thermal expansion being greater than said first coefficient of thermal expansion and said third coefficient of thermal expansion being less than said second coefficient of thermal expansion so as to cause a tensile strain in said channel, said tensile strain causing said increase in said carrier mobility.

Claim 29 (new): The FET of claim 28 further comprising a second gate dielectric situated between said first gate dielectric and said substrate, said second gate dielectric having a third coefficient of thermal expansion, said third coefficient of thermal expansion being less than said first coefficient of thermal expansion and said second coefficient of thermal expansion being greater than said first coefficient of

PAGE 8/11 * RCVD AT 11/5/2009 6:35:38 PM [Eastern Standard Time] * SVR:USPTO-EFXRF-6/21 * DNIS:2738300 * CSID:949 282 1002 * DURATION (mm-ss):02-38

thermal expansion so as to cause a tensile strain in said channel, said tensile strain causing said increase in said carrier mobility.

Claim 30 (new): The FET of claim 28 further comprising a gate liner situated adjacent to said gate stack and a gate spacer situated adjacent to said gate liner, said gate liner having a third coefficient of thermal expansion and said gate spacer having a fourth coefficient of thermal expansion, said fourth coefficient of thermal expansion being greater than said third coefficient of thermal expansion so as to cause a tensile strain in said channel.

PAGE 9/11 * RCVD AT 11/5/2009 6:35:38 PM [Eastern Standard Time] * SVR:USPTO-EFXRF-6/21 * DNIS:2738300 * CSID:949 282 1002 * DURATION (mm-ss):02-38